

F **S**

15GN03MA

- High Cut-off Frequency: $f_T = 1.5$ GHz Typ
- High Gain: $|S_{21e}|^2 = 13$ dB Typ ($f = 1$ GHz)
-

I_C , COLLECTOR CURRENT (mA)

V_{CE} , COLLECTOR-TO-EMITTER VOLTAGE (V)

-

h_{FE} , DC CURRENT GAIN

I_C , COLLECTOR CURRENT (mA)

-

C_{ob} , OUTPUT CAPACITANCE (pF)

V_{CB} , COLLECTOR-TO-BASE VOLTAGE (V)

-

I_C , COLLECTOR CURRENT (mA)

V_{BE} , BASE-TO-EMITTER VOLTAGE (V)

-

f_T , GAIN-BANDWIDTH PRODUCT (GHz)

I_C , COLLECTOR CURRENT (mA)

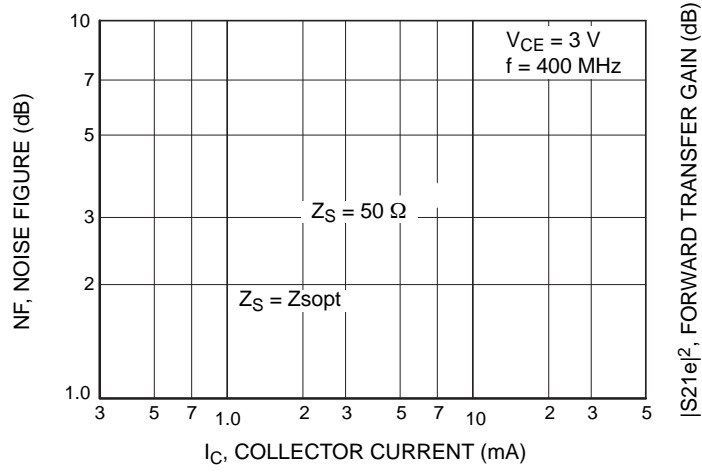
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C_{re} , REVERSE TRANSFER CAPACITANCE (pF)

V_{CB} , COLLECTOR-TO-BASE VOLTAGE (V)

-



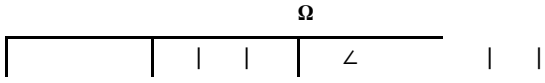


$|S_{21e}|^2$, FORWARD TRANSFER GAIN (dB)

I_C , COLLECTOR CURRENT (mA)

P_C , COLLECTOR DISSIPATION (mW)

T_A , AMBIENT TEMPERATURE ($^{\circ}\text{C}$)



Ω

		∠		∠		∠		∠
100	0.648	-111.11	13.755	118.07	0.025	49.17	0.710	-

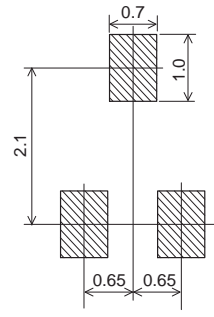


Ω

		∠		∠		∠		∠
100	0.574	-141.90	16.518	106.28	0.017	56.75	0.594	-17.60
200	0.584	-161.69	8.702	92.68	0.024	65.21	0.541	-16.13
300	0.587	-169.42	5.851	85.19	0.033	71.56	0.531	-16.69
400	0.596	-174.12	4.433	79.42	0.042	77.01	0.532	-18.41
500	0.599	-177.29	3.570	74.54	0.053	82.34	0.536	-20.78
600	0.609	179.93	2.987	70.07	0.063	84.47	0.545	-23.60
700	0.616	177.48	2.574	65.88	0.073	86.83	0.550	-26.54
800	0.621	175.27	2.268	61.99	0.085	88.18	0.559	-29.78
900	0.631	173.12	2.033	58.20	0.096	90.72	0.571	-33.08
1000	0.638	170.96	1.845	54.81	0.111	91.80	0.582	-36.46

Ω

		∠		∠		∠		∠
100	0.578	-151.54	16.222	102.78	0.015	58.15	0.564	-16.24
200	0.596	-166.79	8.428	90.13	0.023	71.59	0.524	-14.78
300	0.603	-172.63	5.641	82.89	0.033	76.27	0.520	-15.94
400	0.611	-176.28	4.254	77.21	0.043	79.95	0.521	-17.71
500	0.618	-178.98	3.421	72.11	0.052	83.78	0.530	-20.31
600	0.629	178.44	2.851	67.60	0.064	86.83	0.538	-23.39
700	0.639	176.23	2.452	63.15	0.074	88.24	0.546	-26.40
800	0.647	174.01	2.155	59.33	0.087	89.54	0.555	-29.74
900	0.657	171.87	1.921	55.44	0.099	92.59	0.568	-33.37
1000	0.664	169.65	1.740	51.95	0.113	94.10	0.581	-36.94

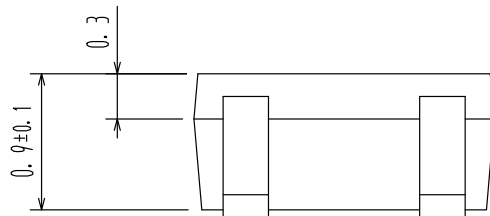
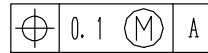
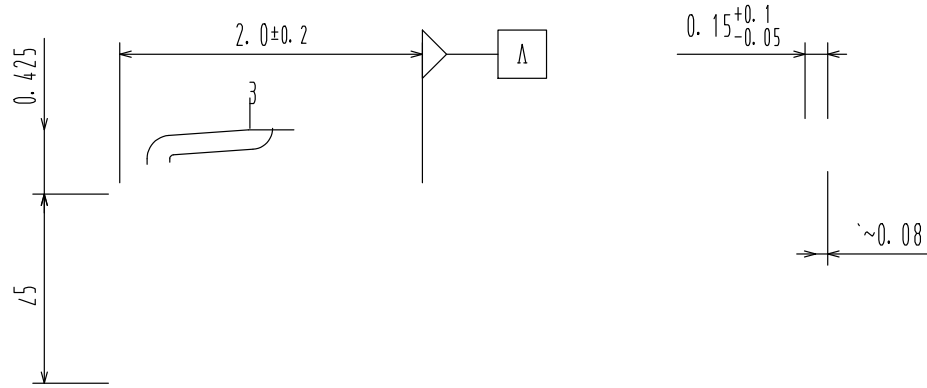


Unit: mm



SC-70 / MCP3
CASE 419AJ
ISSUE O

DATE 30 NOV 2011



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